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Qualcomm Launches First Chips with Integrated CMOS Power Amplifier and Antenna Switch for 3G/4G LTE multiband Mobile Devices

-- Qualcomm Technologies' QFE2320 and QFE2340 chips enable sleeker mobile devices, global multimode LTE roaming and is key component of Qualcomm RF360 Front End Solution --

SAN DIEGO, Feb. 24, 2014 /PRNewswire/ -- Qualcomm Incorporated (NASDAQ: QCOM) today announced that its wholly-owned subsidiary, Qualcomm Technologies, Inc., in cooperation with ZTE, launched the world's first multimode, multiband chip featuring an integrated CMOS power amplifier (PA) and antenna switch on ZTE's new flagship smartphone, the Grand S II LTE.

The successful commercialization of Qualcomm Technologies' QFE2320 and QFE2340 marks a significant step forward for mobile RF front end technology by enabling unprecedented functionality on integrated circuits with simplified routing and one of the smallest PA/antenna switch footprints in the industry. The QFE2320 Multi-mode Multi-band Power Amplifier (MMMB PA) with Integrated Antenna Switch and QFE2340 High Band MMMB PA with integrated Transmitter/Receiver mode switch, are key components – along with QFE1100, the first envelope tracking (ET) chipset for 3G/4G LTE mobile devices – of the Qualcomm® RF360™ Front End Solution, which enables OEMs to create a single multimode design for worldwide LTE mobility. The combination of QFE2320 and QFE2340 covers transmission on all major cellular modes including LTE TDD/FDD, WCDMA/HSPA+, CDMA 1x, TD-SCDMA, and GSM/EDGE and associated RF bands spanning the frequency range from 700 MHz to 2700 MHz. The QFE1100 already has launched in a number of commercial smartphones globally, and is included in the Grand S II LTE.

"The launch of our integrated power amplifier and antenna switch, and our high band power amplifier in the Grand S II LTE, is an exciting development that demonstrates continued execution on the RF360 Front End solution," said Alex Katouzian, senior vice president of product management, Qualcomm Technologies, Inc. "Consumers and OEMs both will benefit from these innovative RF solutions, which will lead to smaller form factors, improved power efficiency and LTE devices capable of global roaming."

"Qualcomm Technologies' RF chipsets are engineered for performance and efficiency, allowing us to design sleeker devices that consume less power, while connecting to the fastest networks worldwide," said June Wang, VP of Strategic Partnership & Global High Tech Team Lead, ZTE. "We're excited to be including both of Qualcomm Technologies' latest RF360 front-end solutions, along with the Qualcomm® Snapdragon™ 800 processor and WTR1625 transceiver, in the Grand S II LTE for best-in-class LTE connectivity and a superior user experience."

The QFE2320 and QFE2340 are fabricated using a CMOS process, which allows for tighter integration of components in a single piece of silicon. The integration of the power amplifier and antenna switch in the QFE2320 simplifies routing, reduces the number of RF components in the front end, and makes for a smaller printed circuit board (PCB) area requirement – all of which allow OEMs to economically create smaller device designs that support the wide range of radio frequencies needed to connect to major 2G, 3G, and 4G LTE networks worldwide. The QFE2340 High Band MMMB PA integrates Transmitter/Receiver mode switches, which offers the world's first commercial LTE Wafer Level Nano Scale Package (WL NSP) MMMB PA and introduces an innovative LTE TDD RF Front end architecture to the mobile industry for the first time.

The QFE2320 and QFE2340 are now shipping to OEMs and are expected to appear in more leading smartphones globally this year. QFE1100, first envelope tracker for 3G/4G LTE devices and QFE1510, configurable antenna matching tuner are two other chips of Qualcomm RF360 solution that were launched commercially in 2013.

About Qualcomm Incorporated
Qualcomm Incorporated (NASDAQ: QCOM) is a world leader in 3G, 4G and next-generation wireless technologies. Qualcomm Incorporated includes Qualcomm's licensing business, QTL, and the vast majority of its patent portfolio. Qualcomm Technologies, Inc., a wholly-owned subsidiary of Qualcomm Incorporated, operates, along with its subsidiaries,

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